

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1462619	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/05 14:36
L2	1462619	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/05 14:36
L3	5	2 and ((high k dielectric) with ((wet chemical) or (wet near treatment)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/05 14:46
L4	1949	2 and ((high k dielectric) or (high k gate dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/05 15:36
L5	5	4 and (cap\$4 with thick\$4 with (high k dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/05 14:53
L6	28	4 and (cap\$4 with (high k dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/05 14:54
L7	0	4 and (capping with (high k dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/05 14:56
L8	11	4 and (capping same (high k dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/05 14:57
L9	9	8 and (oxygen or oxidation or oxidizing)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/05 15:04
L10	9	8 and (oxygen or oxidation or oxidizing) and thick\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/05 15:04

L11	101	2 and (((high k dielectric) or (high k gate dielectric)) with ((atomic layer deposition) or ALD))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/05 15:43
L12	24	11 and (thick\$4 with monolayer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/05 15:44
L13	0	11 and (cap\$5 with thick\$4 with monolayer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/05 15:44